

# 師資介紹



顏志峰 (YEN, CHIH-FENG)

職稱： 副教授

最高學歷： 國立中山大學電機工程研究所博士

學術專長： 金氧半元件製程與分析、化合物半導體、太陽能電池

分機： 23374

參考資料目錄:

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A. Journal Paper - SCI (期刊論文)

B. Journal Paper - EI (期刊論文)

C. Conference Paper (會議論文)

D. Patent (專利)

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A. Journal Paper - SCI (期刊論文)

A1. Ming-Kwei Lee, **Chih-Feng Yen**\*(通訊作者), and Min-Yen Yeh, "High Quality of Liquid Phase-Deposited SiON on GaAs MOS Capacitor with Multiple Treatments". *Journal of Electronic Materials*. Vol. 45, no. 8, 4270-4274. August 2016 (SCI, Impact Factor 1.491, Material Science-coating & Films 5/17)

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- A7. Ming-Kwei Lee, Chen-Lin Ho, Chia-Chi Lin, Nai-Roug Cheng, Ming-Hsuan Houg, Yu-Kai Chien, and **Chih-Feng Yen**, “Light Extraction Efficiency Enhancement of GaN Blue LED with ZnO Nanotips Prepared by Aqueous Solution Deposition”, *J. Electrochem. Soc.*, Vol. 158, No. 5, D286-D289. 2011. (SCI, Impact Factor 2.42, Material Science-coating & Films 1/18)
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- A9. Ming-Kwei Lee and **Chih-Feng Yen**, “Characterization of Fluorinated-SiO<sub>2</sub>/PMA-treated TiO<sub>2</sub>/(NH<sub>4</sub>)<sub>2</sub>S-treated GaAs MOS Structure”, *J. Electrochem. Soc.*, Vol. 158, no. 8, G199-G202, 2011. (SCI, Impact Factor 2.42, Material Science-coating & Films 1/18)
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- B3. Ming-Kwei Lee, **Chih-Feng Yen\*(通訊作者)**, “InP Schottky Barrier MOSFET with TiO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> as Gate Oxide”, **IEEE IS3C2014** International Symposium on Computer, Consumer and Control. IEEE Computer Society. Page 573-576.

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C. Conference Paper (會議論文)

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- C1. Ming-Kwei Lee, Jung-Jie Huang, and **Chih-Feng Yen**, “Low Leakage Current and High Dielectric Constant LPD-SiO<sub>2</sub>/MOCVD-TiO<sub>2</sub> Film Grown on (NH<sub>4</sub>)<sub>2</sub>S<sub>x</sub> Treated InP Substrate” The 17th Indium Phosphide and Related Materials Conference (IPRM), Glasgow, Scotland, U.K., 2005.
- C2. Ming-Kwei Lee, **Chih-Feng Yen**, Tsung-Hsiang Shih, Chen-Lin Ho, Hung-Chang Lee, Hwai-Fu Tu and Cho-Han Fan, “Electrical characteristics of fluorine passivated MOCVD-TiO<sub>2</sub> Film on (NH<sub>4</sub>)<sub>2</sub>S<sub>x</sub> treated GaAs”, The Fifth China International Conference on High-Performance Ceramics, Changsha, Hunan Province, China, pp. 30, May (2007).

- C3. Ming-Kwei Lee, Tsung-Hsiang Shih, Chen-Lin Ho, Hung-Chang Lee, **Chih-Feng Yen**, Hwai-Fu Tu and Cho-Han Fan, "Photocatalyses of Nano-scaled ZnSe/TiO<sub>2</sub> and ZnSe/TiO<sub>2</sub> heterojunctions", The Fifth China International Conference on High-Performance Ceramics, Changsha, Hunan Province, China, pp. 188, May (2007).
- C4. Ming-Kwei Lee, **Chih-Feng Yen**, Cho-Han Fan, "Enhancement-mode Si MOSFET with MOCVD-TiO<sub>2</sub> as gate oxide improved by oxygen annealing and fluorine passivation", The International Conference on Thin Film (ICTF14), Ghent, Belgian, 2008, 11, 17 to 2008, 11, 20.
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- C10. Ming-Kwei Lee, Nai-Roug Cheng, Cho-Han Fan and **Chih-Feng Yen**, "Density of ZnO Nanotip Array Controlled by ZnO Seed Layer". 2012 International Conference on Nanomaterials and Electronics Engineering ICNEE 2012, July 24-26, 2012, Kuala Lumpur, Malaysia.
- C11. **Chih-Feng Yen**, Min-Yen Yeh, and Ming-Kwei Lee, "Electrical characteristics InP MOSFET with atomic layer deposited nano-Al<sub>2</sub>O<sub>3</sub> and TiO<sub>2</sub> films as dielectrics", 13th International Conference on N&N, pp. 139, NN16 Conference, Thessaloniki Greece, 5-8 July 2016.
- C12. **Chih-Feng Yen\***, Chun-Fa Hsu, Pei-Wei Chen, Shan-Hsiung Li, "Effect of Hafnium Doping in Indium Zinc Oxide Thin-Film Transistors by Sol-gel Method" 2016 International Conference on Physics and Mechanics of New Materials and Their Applications (PHENMA 2016) pp. 90, Surabaya, Indonesia, July 19-22, 2016.
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- C26. **Chih-Feng Yen\***, Shen-Ming Hu, Wen-Feng Fan, and Yi-Fan Lu, "Preparation of Liquid-Deposited Al<sub>2</sub>O<sub>3</sub>:ZnO/p-Si MOS Structure with Various Alumina Doping Volumes", 2021 International Membrane Conference in Taiwan(2021IMCT), Taoyuan, ROC, May 14, 2021 (延期舉行).
- C27. **Chih-Feng Yen\***, Yi-Fan Lu, Shen-Ming Hu, and Wen-Feng Fan, "Preparation of silicon oxynitride/Si with low interface state density and leakage current by non-vacuum deposition process", 2021 International Membrane Conference in Taiwan(2021IMCT), Taoyuan, ROC, May 14, 2021 (延期舉行).
- C28. **Chih-Feng Yen\***, Wen-Feng Fan, Shen-Ming Hu, and Yi-Fan Lu, "Research on ZnO-doped Y<sub>2</sub>O<sub>3</sub>/Si MOS close to ideal C-V property", 2021 International Membrane Conference in Taiwan(2021IMCT), Taoyuan, ROC, May 14, 2021 (延期舉行).

#### <國內會議期刊>

- C29. **顏志峰**、王美玲、廖怡婷、陳泊勳、姚文洋, "利用液相沉積法製備二氧化矽抗反射層對於染料敏化太陽電池之影響", 2017 第十五屆微電子技術發展與應用研討會, 高雄, 台灣, 13 頁, 中華民國一百零六年五月十九日
- C30. **顏志峰**、陳政成、王泓錡、鄭名軒、徐元伯, "液相沉積法製備 TiO<sub>2</sub> 薄膜應用於 DSSC 阻隔層", 2017 第十五屆微電子技術發展與應用研討會, 高雄, 台灣, 63 頁, 中華民國一百零六年五月十九日
- C31. **顏志峰**、邱嘉輝, "銅線製程對鋅墊受損鋅線參數研究", 2018 第十六屆微電子技術發展與應用研討會, 高雄, 台灣, 47-48 頁, 中華民國一百零七年五月二十五日
- C32. **Chih-Feng Yen<sup>a)</sup>**, Yi-Fan Lu, Shen-Ming Hu, Cheng-Hsien Tsai, Ming-Chih Tsai, "Investigation of magnesium oxide films on silicon substrate with liquid phase deposition," 2019 17th conference on microelectronics and applications, pp. 23, Kaohsiung, Taiwan, May 24, 2019.
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- C34. **Chih-Feng Yen<sup>a)</sup>**, Shen-Ming Hu, Wen-Feng Fan, and Yi-Fan Lu, "Study on the structure of liquid-deposited ZnO/p-Si

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C37. **Chih-Feng Yen<sup>a)</sup>**, and You-Ming Liu, "Research on the warpage change of the small out-line package by the shadow moiré", 2021 19th Conference on Microelectronics Technology & Application, pp.1, Kaohsiung, ROC, May 21, 2021.

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#### D. Patent (專利)

D1. 李明達、黃俊杰和**顏志峰**，“一種高介電常數與低漏電流磷化銦金氧半電容的製作方法”，中華民國，發明專利第 I 249841 號

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